

# 2SK3875-01

## N-CHANNEL SILICON POWER MOSFET

### Outline Drawings (mm) 200407

## FUJI POWER MOSFET Super FAP-G Series

### Features

- High speed switching, Low on-resistance
- Low driving power, Avalanche-proof
- No secondary breakdown

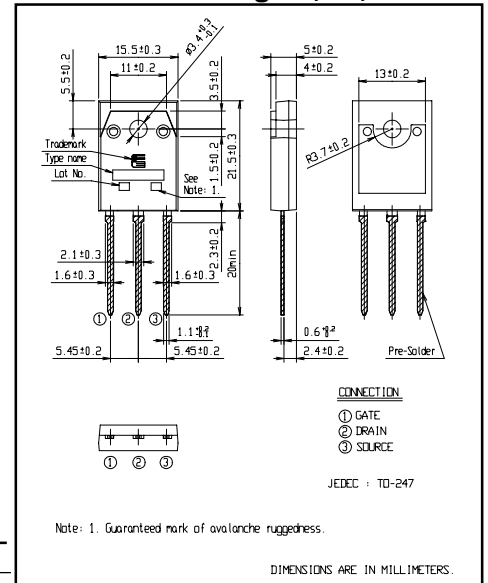
### Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

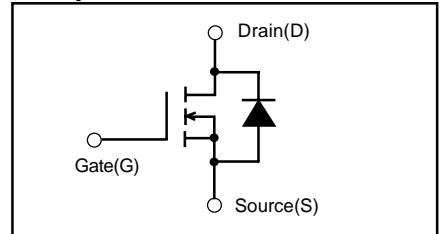
### Maximum ratings and characteristic

#### Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V <sub>DS</sub>	900	V	
	V <sub>Dsx</sub>	900	V	V <sub>GS</sub> =-30V
Continuous Drain Current	I <sub>D</sub>	13	A	
Pulsed Drain Current	I <sub>D(puls)</sub>	±52	A	
Gate-Source Voltage	V <sub>GS</sub>	±30	V	
Non-Repetitive Maximum Avalanche current	I <sub>AS</sub>	13	A	Note *1
Repetitive Maximum Avalanche current	I <sub>AR</sub>	6.5	A	
Non-Repetitive Maximum Avalanche Energy	E <sub>AS</sub>	1006	mJ	Note *2
Repetitive Maximum Avalanche Energy	E <sub>AR</sub>	35.5	mJ	Note *3
Maximum Drain-Source dV/dt	dV <sub>DS</sub> /dt	40	kV/μs	V <sub>DS</sub> ≤ 900V
Peak Diode Recovery dV/dt	dV/dt	5	kV/μs	Note *4
Max. Power Dissipation	P <sub>D</sub>	355	W	T <sub>c</sub> =25°C
		2.50		T <sub>a</sub> =25°C
Operating and Storage Temperature range	T <sub>ch</sub>	+150	°C	
	T <sub>stg</sub>	-55 to +150	°C	



### Equivalent circuit schematic



- Note \*1: T<sub>ch</sub> ≤ 150°C
- Note \*2: Starting T<sub>ch</sub>=25°C, I<sub>AS</sub>=5.2A, L=67.5mH, V<sub>CC</sub>=100V, R<sub>G</sub>=50Ω  
E<sub>AS</sub> limited by maximum channel temperature and Avalanche current.  
See to the 'Avalanche Energy' graph
- Note \*3: Repetitive rating; Pulse width limited by maximum channel temperature.  
See to the 'Transient Thermal impedance' graph.
- Note \*4: I<sub>F</sub> ≤ -I<sub>D</sub>, -di/dt=50A/μs, V<sub>CC</sub> ≤ BV<sub>DSS</sub>, T<sub>ch</sub> ≤ 150°C

### Electrical characteristics (Tc =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA V <sub>GS</sub> =0V	900			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA V <sub>DS</sub> =V <sub>GS</sub>	3.0		5.0	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =900V V <sub>GS</sub> =0V			25	μA
		V <sub>DS</sub> =720V V <sub>GS</sub> =0V			250	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V			100	nA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =6.5A V <sub>GS</sub> =10V		0.79	1.00	Ω
Forward Transconductance	g <sub>fs</sub>	I <sub>D</sub> =6.5A V <sub>DS</sub> =25V	6.0	12		S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V		1750	2625	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		220	330	
Reverse Transfer Capacitance	C <sub>rss</sub>	f=1MHz		13	19.5	
Turn-On Time t <sub>on</sub>	td(on)	V <sub>CC</sub> =600V I <sub>D</sub> =6.5A		20	30	ns
	t <sub>r</sub>	V <sub>GS</sub> =10V		12	18	
Turn-Off Time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10Ω		60	90	
	t <sub>f</sub>			15	22.5	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> =450V		46	69	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =13A		14	21	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V		17	26	
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =13A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.10	1.50	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =13A V <sub>GS</sub> =0V		4.5		μs
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		25		μC

### Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			0.352	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			50.0	°C/W

## Characteristics

